Elektronische Bauelemente

BCX56

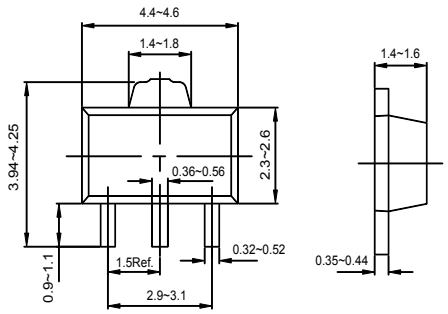
NPN Transistors

Plastic-Encapsulate Transistors

RoHS Compliant Product

1.BASE
2.COLLECTOR
3.EMITTER

SOT-89



Dimension in Millimeter

Features

Power dissipation

$P_{CM:}$ 1.2 W (Tamb=25°C)

Collector current

$I_{CM:}$ 1 A

Collector-base voltage

$V_{(BR)CBO}$: 100 V

Operating and storage junction temperature range

T_J, T_{stg}: -65°C to +150°C

Complimentary to BCX53

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage		$V_{(BR)CBO}$	Ic=100μA, I_E=0	100		V
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	I_C= 1 mA , I_B=0	80		V
Emitter-base breakdown voltage		$V_{(BR)EBO}$	I_E=10μA, I_C=0	5		V
Collector cut-off current		I_{CBO}	V_{CB}=30V, I_E=0		100	nA
Emitter cut-off current		I_{EBO}	V_{EB}=5 V, I_C=0		100	nA
DC current gain	**BCX56**	$h_{FE(1)}$	V_{CE}=2V, I_C= 5mA	63		
	BCX56-10	$h_{FE(2)}$	V_{CE}=2V, I_C= 150mA	63	250	
	BCX56-16	$h_{FE(3)}$	V_{CE}=2V, I_C= 500mA	40		
Transition frequency		f_T	V_{CE}= 5V, I_C= 10mA	100		MHz
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=500 mA, I_B= 50mA		500	mV
Base-emitter voltage		$V_{BE(ON)}$	I_C= 500 mA, V_{CE}=2V		1	V

Classification of h_{FE2}

Rank	10	16
Range	63 - 160	100 - 250

DEVICE MARKING	BCP56 xxxx ← Date Code

Characteristics Curve